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# Eliminating optical bounce of homeotropic liquid crystal cells with sputtered silicon dioxide alignment films by rubbing treatment

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# 1. Introduction

Homeotropic alignment of LCs is widely used for LCD mass production due to its excellent contrast ratio. With compensation films and multidomain vertical alignment (MVA) technique, the oblique light leakage of homeotropic LC cell could be decreased to offer a wide viewing angle in LCD application [\[1–3\].](#page--1-0) However, the long response time of homeotropically aligned LC cell is still needed to be solved. Pieranski et al. posed that the flow motion would occur to induce the twist structure of the LC cell when it undergoes transition from homeotropic to planar state [\[4\]](#page--1-0). It has been investigated that LC flow effect is a crucial factor for causing long response time in homeotropic cells. This phenomenon is also called the back flow effect. [Fig. 1](#page-1-0) shows the process of flow motion. When the electric field varies rapidly, fast rotation of LCs in the middle of LC cell produces a torque which results in a tipping over of the LC director near the substrates [\[5\].](#page--1-0) The flow motion would lead the director of LCs near the substrates to tilt in the opposite direction, that is, the flow causes the tilt angle of LCs to be over  $90^\circ$  from the substrate. In 1970s, Berreman and van Doorn numerically derived the equation of motion for LCs based on the continuum theory of Ericksen and Leslie [\[6–9\]](#page--1-0). They pointed out the calculated transient electrooptic (EO) curve has the optical bounce if the flow effect was considered [\[10\].](#page--1-0) It discloses that the flow motion plays the key

#### **ABSTRACT**

In this article, we propose a mechanical rubbing method to eliminate the optical bounce and decrease the response time of homeotropic liquid crystal (LC) cells with sputtered silicon dioxide alignment films. After gently rubbing the inorganic alignment film (sputtered silicon oxide,  $SiO<sub>2</sub>$ ), the decreasing polar anchoring energy results in slightly smaller pretilt angle which gives LC a toppling direction to shorten the transition time while LC cell is applied by an external electric field. The results of our work show that this rubbing remedy can suppress the optical bounce. This simple and efficient surface treatment could be applied to liquid crystal on silicon (LCOS) technique for high resolution microdisplays and portable electronic products.

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role in the appearance of the bounce. In addition, low azimuthal anchoring energy of homeotropic alignment would produce the azimuthal alignment error. Recently, Chen et al. found that azimuthal alignment error is another important factor generating the twist structure throughout the LC cell [\[11\].](#page--1-0) In practice, the azimuthal alignment error could not be ignored even the angle is just as small as  $0.1^{\circ}$ . Combination of the flow motion and azimuthal alignment error would result in the optical bounce on the transient EO curve. Once the flow motion or azimuthal alignment error was omitted, the bounce disappears and the transmission coefficient T varies monotonically. The optical bounce induced from LC twist structure increases the response time of LC cells to several 100 ms which is unsuitable for motion-image LCDs. Many research groups and manufacturers are devoted to the issue of dissipating optical bounce. Though multidomain alignment with a protrusion could circumvent the optical bounce, it requires several lithographic steps. On the other hand, controlling the wave forms of the applied voltages in the rising period has been proposed to slow down the fast rotation of LCs in the middle region and remove the flow effect. However, it is not a simple task for LCD application [\[5,11\]](#page--1-0). In this article, we utilize cloth rubbing on silicon oxide surface to eliminate the optical bounce. Gently rubbing increases the azimuthal anchoring energy and induces LCs near the substrates to align with a higher azimuthal accuracy and smaller pretilt angle (the angle between the LC director and the substrate). A smaller pretilt angle corresponds to a weaker polar anchoring energy but a stronger azimuthal anchoring strength. The transient EO curve rising smoothly verifies that we perform a successful mechanical method removing the optical bounce efficiently. This method could be applied to LCOS for its reduction in processing complexity.





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Fig. 1. Schematic of the process of flow motion. While the electric field is applied, fast rotation of LC in the middle region would produce a torque to result in a tipping over of the LC director near the substrates. After a moment, LC would turn back to its equilibrium position.

**Table** 

### 2. Experimental details

### 2.1. Sample preparation

Instead of employing vertical alignment (VA) polyimide, we uti-lized sputtered-SiO<sub>2</sub> film for LC alignment [\[12\].](#page--1-0) This inorganic alignment layer has above average durability avoiding damage from high-temperature environment and long-time UV light exposure. Here, we used the indium tin oxide glass as the substrates and sputtered-SiO<sub>2</sub> film as alignment film on the substrates with  $90^{\circ}\,$  deposition  $\,$  angle  $\,$  (RF $\sim$ 13.56 MHz,  $\,$  pressure $\sim$ 10 mtorr,  $\,$  and power $\sim$ 200 watts). Because the sputtered-SiO $_2$  film is thin and transparent, it could be applied to both transmissive and reflective LCDs. The induced dipole–dipole interaction deduced from Van der Waals force dominates the LC alignment on the  $SiO<sub>2</sub>$  film. This vertical sputtering deposition using  $SiO<sub>2</sub>$  keeps the negative LCs to be at the field-off homeotropic dark state under crossed polarizers [\[13\].](#page--1-0) After sputtering, the SiO<sub>2</sub> film (the thickness is  $\sim$ 105 nm) was gently rubbed with velvet to enhance the LC azimuthal anchoring strength. Thus LCs would be led to align in the rubbing direction to decrease the transition time for the twist structure when the electric field is turned on. The LC material used here was MLC-6609 (from Merck) which has negative dielectric anisotropy (for laser wavelength  $\lambda$  = 632.8 nm, ne = 1.5514, no = 1.4737,  $\Delta \epsilon$  = -3.7, K33 = 17.9  $\times$  10<sup>-12</sup> N/m). Then the two substrates were assembled into anti-parallel cells with  $\sim$ 4  $\mu$ m cell gap to be observed under the crossed polarizers. And the angle between the rubbing direction and the transmitted axis of the front polarizer was 45°. Therefore the cell would be at the field-on bright state. The threshold voltage of our cells filled with MLC-6609 is measured around 2.3 volts, which is consistent with the calculated result [\[14\].](#page--1-0)

# 2.2. Electro-optical curve properties

We fabricated several cells with different rubbing depth and rubbing strength (see Table 1) to compare their electro-optical properties. Though glassy spacers in three cells are the same size  $(4 \mu m)$ , there are still slight variations in these cell gaps after being fabricated by hands. In Table 1, the A cell is unrubbed and the rubbing depth of the C cell is 200 µm deeper than the B cell. Rubbing strength (RS) relates to the rubbing depth  $(M)$  as follow:

$$
RS = M(2\pi n r/v - 1),\tag{1}
$$

where  $n$  is the rotation frequency of the roller,  $r$  is radius of the roller and  $v$  is translating speed of the substrate[.\[15\]](#page--1-0) According to the relation, B cell has RS $\sim$ 187 mm (M $\sim$ 1 mm,  $r$  = 30 mm,  $n$  = 10 Hz,  $v = 7$  mm/s) and C cell has  $RS \sim 225$  mm ( $M \sim 1.2$  mm, other parame-







ters are identical to those of B cell). The larger rubbing depth corresponds to the larger rubbing strength. In Table 1, we describe the rubbing strength of A, B, and C cells to be unrubbed, mildly rubbed, and moderately rubbed which is easy for description as follows. Fig. 2 shows the rising time versus applied voltage of these three LC cells. The rising time is defined as the period that the transmission curve undergoes from 10% to 90% while applying with a saturated voltage.[\[14\]](#page--1-0) When the voltage is lower than 5.8 volts, the rubbing strength does not have significant influence on the rising time. In this situation, the rising time is basically dominated by the cell gap. Due to the larger cell gap, the rising time of B cell is a little longer than those of other cells. If the applied voltage is larger than 5.8 volts, the rising time of the rubbed- and unrubbed- $SiO<sub>2</sub>$ cells would become very different. Upon increasing applied voltage, the rising time of the rubbed-SiO<sub>2</sub> cells maintains less than 50 ms,



Fig. 2. The rising time vs. applied voltage. When the voltage is lower than 5.8 volts, the cell gap dominates the rising time. Thicker cell gap (B cell) causes the rising time a little longer. With the applied voltage larger than 5.8 volts, the rising time of the rubbed-SiO<sub>2</sub> cells maintains less than 50 ms and that of the unrubbed-SiO<sub>2</sub> cells increases greatly to 500 ms.

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